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SEP 27 2007

Amendments to Specification:

Please add the following new paragraph after paragraphs 15 and 55 respectively:

[0015.1] Figure 7 shows a flowchart of a method in accordance with an embodiment of the present invention.

[0055.1] For an example of an alternate embodiment, please refer now to Figure 7. Figure 7 is a flowchart of a method in accordance with an alternate embodiment. Step 701 includes measuring values associated with a plurality of memory elements, wherein the values are indicative of a digital state. Step 702 includes calculating a plurality of terms associated with transitions in the values between memory elements wherein calculating includes calculating a sum of terms associated with transitions. Step 703 involves determining the digital state of at least one memory element using the calculations from step 702 by determining the digital states of a memory word by choosing an outcome that minimizes the sum of transition-terms.

Please replace paragraphs 22 and 23 with the following amended paragraphs:

[0022] Some embodiments may employ adaptive threshold techniques to keep track of resistive values associated with each memory element while interpreting successive memory elements in the memory array. In this manner, measurements of proximate memory elements may be exploited to improve accuracy of subsequent measurements. FIG. 2 shows an illustrative example of a memory 250. The memory 250 includes a memory array 200 that comprises memory elements 202A-F, which may employ adaptive threshold embodiments. Note that the example depicted in FIG. 2 is meant to be merely illustrative and should not be construed as limiting in scope.

[0023] Each memory element 202A-F may contain a digital value (DV), that may be represented, for example by a resistance R. Because the array 200 may be constructed using semiconductor processing techniques, the resistance representing the digital value of one memory element may deviate from the resistance representing the same digital value in another memory element. This deviation is illustrated in FIG. 2 by the different resistive

values shown for each memory element. In an embodiment, the memory 250 also includes circuitry 210 such as a comparison circuit 204 and a register 206. Accordingly, ~~In~~ when reading the digital value, ~~a~~ the comparison circuit 204 may compare the memory element's resistive value to a predetermined threshold value contained in register 206, which may produce an output signal indicating the memory element's digital value.